



Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

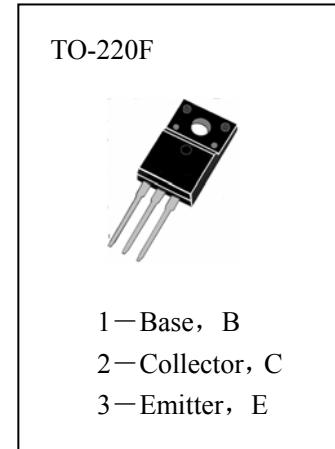
HP31CF

■ APPLICATIONS

Medium Power Linear switching Applications.

■ ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

T_{stg} —Storage Temperature.....	-55~150°C
T_j —Junction Temperature.....	150°C
P_C —Collector Dissipation ($T_c=25^\circ\text{C}$).....	30W
P_C —Collector Dissipation ($T_a=25^\circ\text{C}$)	2W
V_{CBO} —Collector-Base Voltage.....	100V
V_{CEO} —Collector-Emitter Voltage.....	100V
V_{EBO} —Emitter-Base Voltage.....	5V
I_C —Collector Current (DC)	3A
I_C —Collector Current (Pulse)	5A
I_B —Base Current.....	1A



■ ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CEO}	Collector-Emitter Breakdown Voltage	100			V	$I_C=30\text{mA}, I_B=0$
HFE (1)	*DC Current Gain	25				$V_{CE}=4\text{V}, I_C=1\text{A}$
HFE (2)	*DC Current Gain	10		50		$V_{CE}=4\text{V}, I_C=3\text{A}$
$V_{CE(sat)}$	*Collector- Emitter Saturation Voltage			1. 2	V	$I_C=3\text{A}, I_B=375\text{mA}$
$V_{BE(ON)}$	*Base-Emitter On Voltage			1. 8	V	$V_{CE}=4\text{V}, I_C=3\text{A}$
I_{CEO}	Collector Cut-off Current			0. 3	mA	$V_{CB}=60\text{V}, I_B=0$
I_{CES}	Collector Cut-off Current			200	μA	$V_{CE}=100\text{V}, V_{EB}=0$
I_{EBO}	Emitter Cut-off Current			1	mA	$V_{EB}=5\text{V}, I_C=0$
f_T	Current Gain-Bandwidth Product	3. 0			MHz	$V_{CE}=10\text{V}, I_C=0.5\text{A}, f=1\text{MHz}$

*Pulse Test: $PW \leqslant 300 \mu\text{s}$, Duty cycle $\leqslant 2\%$



Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

HP31CF

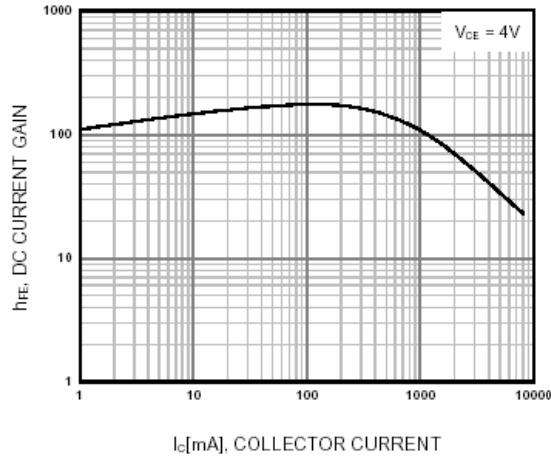


Figure 1. DC current Gain

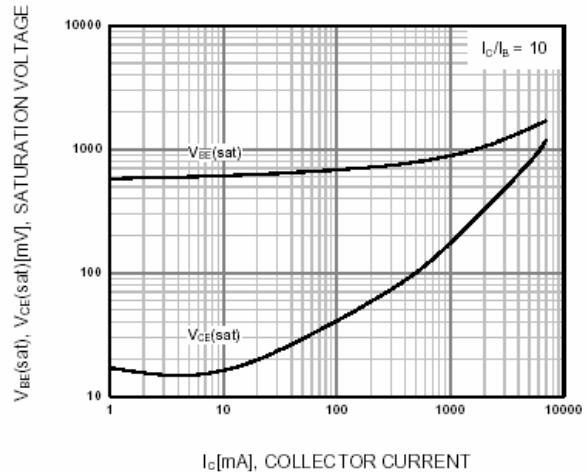


Figure 2. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

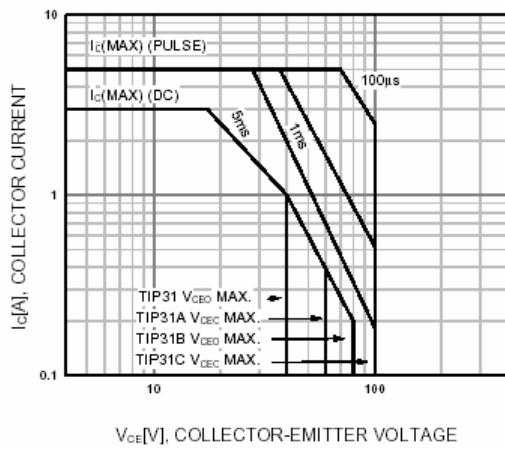


Figure 3. Safe Operating Area

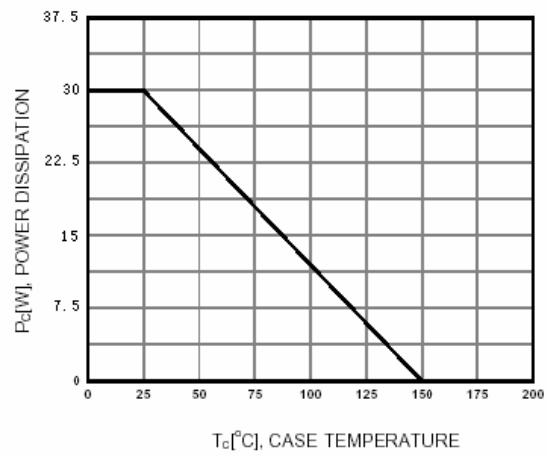


Figure 4. Power Derating